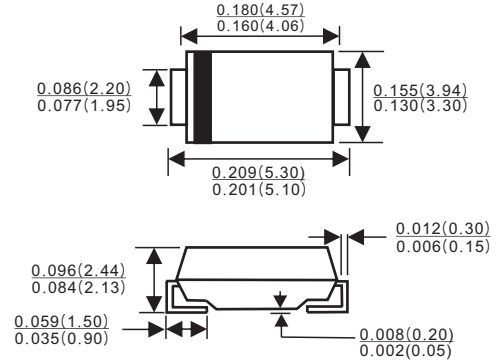




### SMB/DO-214AA

#### Features

- ✦ Glass passivated junction chip
- ✦ For surface mounted applications
- ✦ Low profile package
- ✦ Built-in strain relief
- ✦ Ideal for automated placement
- ✦ Easy pick and place
- ✦ Super fast recovery time for high efficiency
- ✦ Glass passivated chip junction
- ✦ High temperature soldering:  
260°C/10 seconds at terminals
- ✦ Plastic material used carries Underwriters  
Laboratory Classification 94V-0



#### Mechanical Data

- ✦ Cases: Molded plastic
- ✦ Terminals: Pure tin plated, lead free.
- ✦ Polarity: Indicated by cathode band
- ✦ Weight: 0.21 gram

Dimensions in inches and(millimeters)

### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

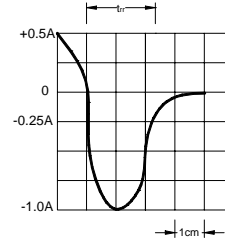
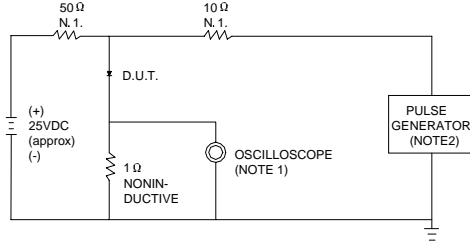
For capacitive load, derate current by 20%

Type Number	Symbol	ES 3A	ES 3B	ES 3C	ES 3D	ES 3F	ES 3G	ES 3H	ES 3J	ES 3K	ES 3M	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	150	200	300	400	500	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	105	140	210	280	350	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	150	200	300	400	500	600	800	1000	V
Maximum Average Forward Rectified Current See Fig. 1	$I_{(AV)}$	3.0										A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method) @ $T_L = 100^\circ\text{C}$	$I_{FSM}$	100										A
Maximum Instantaneous Forward Voltage @ 3.0A	$V_F$	0.95			1.3			1.7			V	
Maximum DC Reverse Current @ $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$	$I_R$	10					500					uA uA
Maximum Reverse Recovery Time ( Note 1 )	$T_{rr}$	35						75				nS
Typical Junction Capacitance ( Note 2 )	$C_j$	45					30					pF
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$ $R_{\theta JL}$	47					12					$^\circ\text{C} / \text{W}$
Operating Temperature Range	$T_J$	-55 to +150										$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to +150										$^\circ\text{C}$

- Notes:
1. Reverse Recovery Test Conditions:  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{RR}=0.25\text{A}$
  2. Measured at 1 MHz and Applied  $V_R=4.0$  Volts
  3. Units Mounted on P.C.B. with 0.6" x 0.6"(16mm x 16mm) Copper Pad Areas

### Ratings AND Characteristic Curves

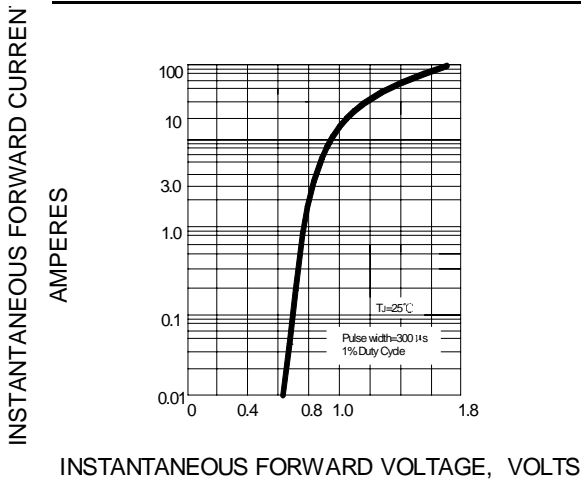
**FIG.1 -- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC**



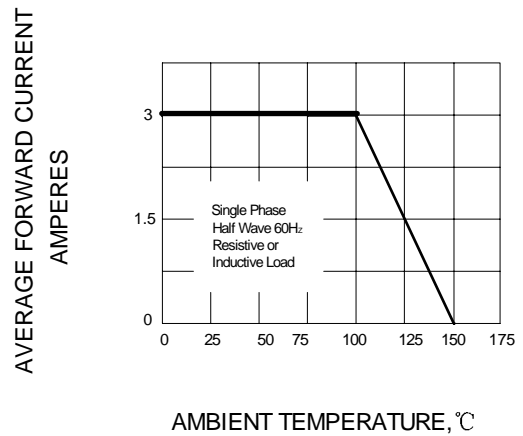
NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE = 1MΩ .22pF.  
2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 Ω .

SET TIME BASE FOR 20/30 ns/cm

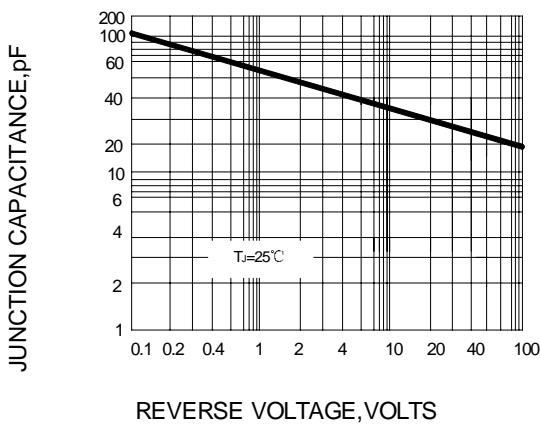
**FIG.2 -- TYPICAL FORWARD CHARACTERISTIC**



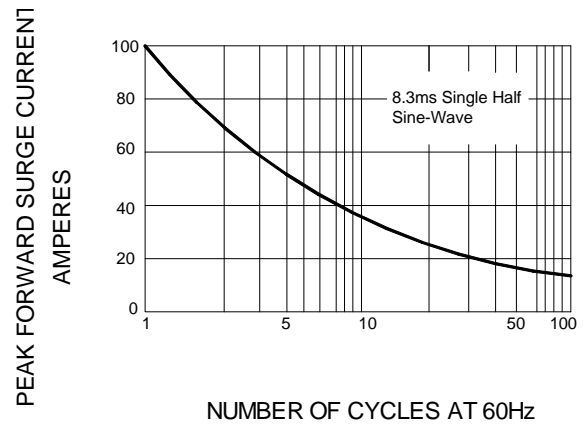
**FIG.3 -- FORWARD DERATING CURVE**



**FIG.4 -- TYPICAL JUNCTION CAPACITANCE**



**FIG.5 -- PEAK FORWARD SURGE CURRENT**



PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
SMB	3000/REEL	48000	36X35.8X36.5	12.00	11.00



**LGE**

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## 产品本体印字图示

### 标识

